

ABSTRACT

The present invention relates to a structure for ground connection on a component including a vertical MOS power transistor and logic components, the substrate of a first type of conductivity of the component corresponding to the drain of the MOS transistor and the logic components being formed in at least one well of the second type of conductivity and on the upper surface side of the substrate. In the logic well, a region of the first type of conductivity is formed, on which is formed a metallization, to implement, on the one hand, an ohmic contact, and on the other hand, a rectifying contact.

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